

# ZK2500-RECTIFIER DIODE

Jiangsu Yangjie Runau Semiconductor Co.,Ltd

2000-3000 V<sub>RRM</sub>

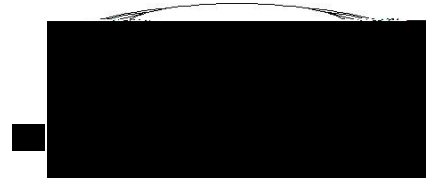
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## FAST RECOVERY RECTIFIER DIODE

### Features:

ZT80cT

- . All diffused structure
- . High surge rating
- . Blocking capability up to 3000 volts
- . Soft recovery
- . Ceramic housing hermetic package
- . Pressure assembled device



## ELECTRICAL CHARACTERISTICS AND RATINGS

### Reverse Blocking

V<sub>RRM</sub> = Repetitive peak reverse voltage

V<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I <sub>RRM</sub>	15 mA 80 mA (3)
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### Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	I <sub>F(AV)</sub>		2500		A	Sinewave 180°, T <sub>c</sub> = 70
RMS forward current	I <sub>FRMS</sub>		3925		A	
Peak one cycle surge (non repetitive) current	I <sub>FSM</sub>		38000		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T <sub>j</sub> = 125
I square t	I <sup>2</sup> t		7220000		A <sup>2</sup> s	8.3 msec and 10.0 msec
Peak forward voltage	V <sub>FM</sub>		2.40		V	I <sub>FM</sub> = 3000A; Duty cycle 0.01%
Reverse Recovery Current (4)	I <sub>RM(REC)</sub>		*		A	I <sub>FM</sub> = 1000 A; dI <sub>F</sub> /dt = 10 A/ s; T <sub>j</sub> max
Reverse Recovery Charge (4)	Q <sub>rr</sub>		*		μC	I <sub>FM</sub> = 1000 A; dI <sub>F</sub> /dt = 10 A/ s; T <sub>j</sub> max
Reverse Recovery Time (4)	t <sub>rr</sub>		8		μs	I <sub>FM</sub> = 1000 A; dI <sub>F</sub> /dt = 10 A/ s; T <sub>j</sub> max

\* For guaranteed maximum values, contact factory

**Jiangsu Yangjie Runau Semiconductor Co., Ltd**